

## Dual N-Channel 60 V (D-S) 175 °C MOSFET

### DESCRIPTION

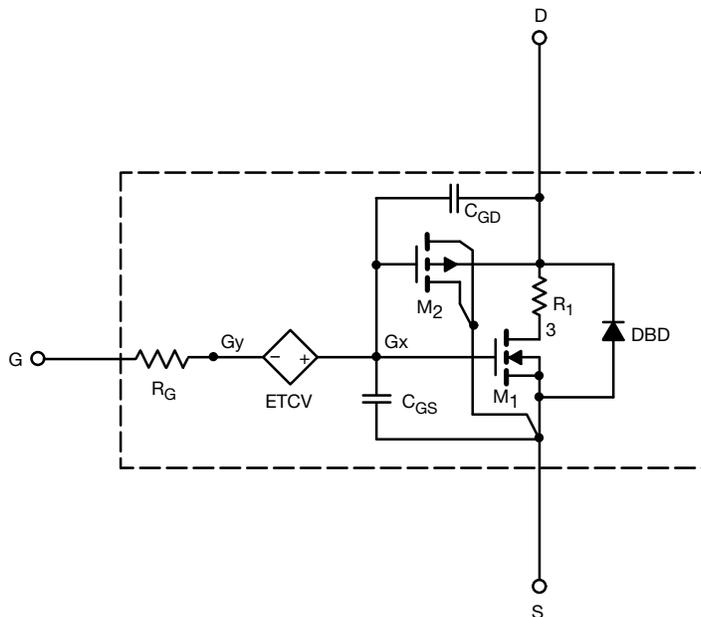
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

### SUBCIRCUIT MODEL SCHEMATIC



### Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



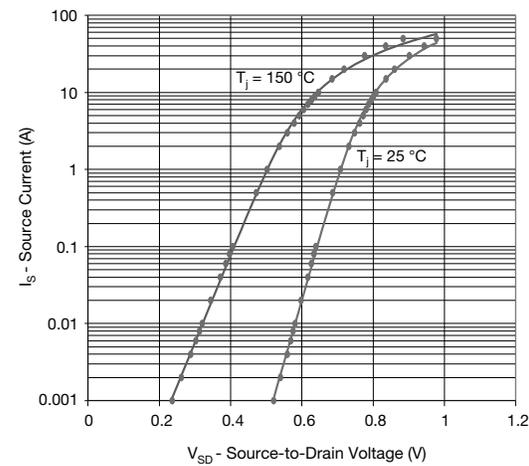
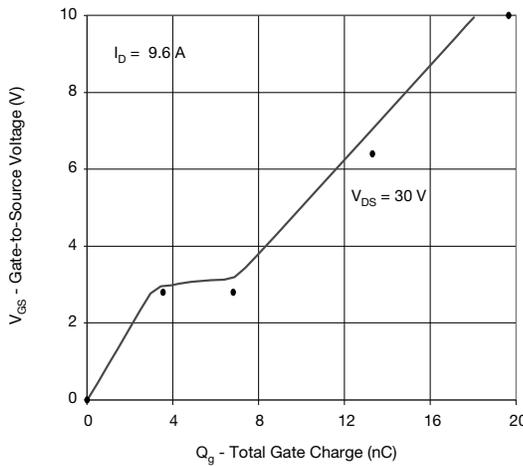
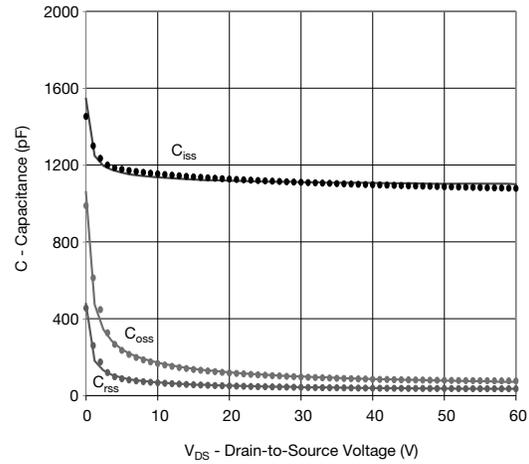
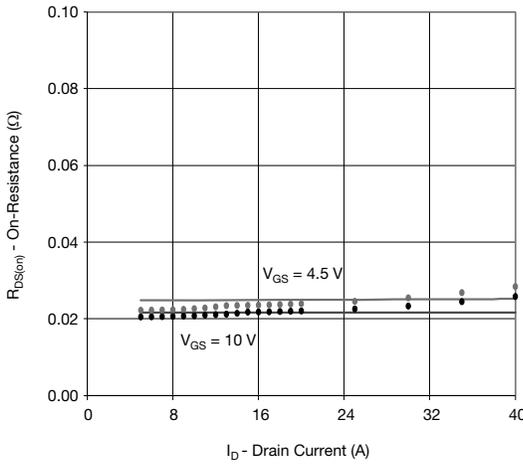
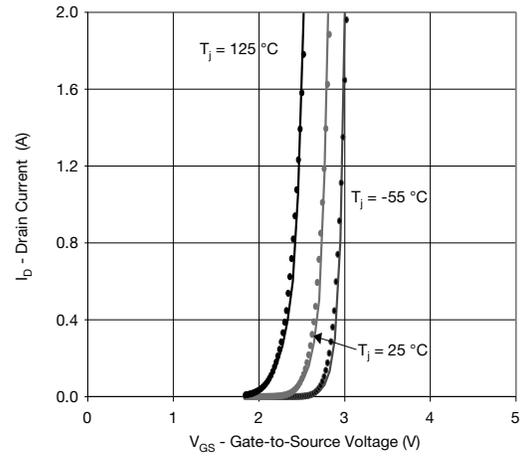
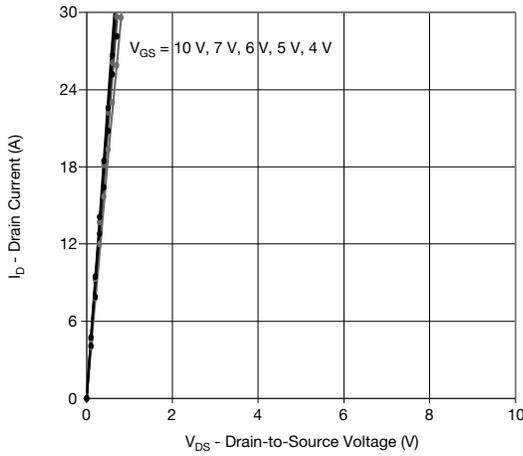
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
<b>Static</b>					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	2	V
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5.2\text{ A}$	0.0216	0.0223	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	0.0248	0.0242	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 5.2\text{ A}$	30	19	S
Diode Forward Voltage	$V_{SD}$	$I_S = 3.6\text{ A}$	0.76	0.76	V
<b>Dynamic<sup>b</sup></b>					
Input Capacitance	$C_{iss}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	1110	1113	pF
Output Capacitance	$C_{oss}$		100	100	
Reverse Transfer Capacitance	$C_{rss}$		45	44	
Total Gate Charge	$Q_g$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 9.6\text{ A}$	1.3	20	nC
Gate-Source Charge	$Q_{gs}$		3.5	3.5	
Gate-Drain Charge	$Q_{gd}$		3	3	

**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.



## COMPARISON OF MODEL WITH MEASURED DATA ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



### Note

- Dots and squares represent measured data.